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PTO-1449 (Modified) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT	ATTY. DOCKET NO. 211.001-D1-US	SERIAL NUMBER 10/694,689
	APPLICANT(S) Fazan et al.	
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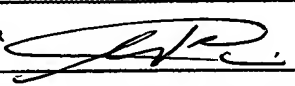
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WSL	4,032,947	6/1977	Kesel et al.			
	3,997,799	12/1976	Baker			
	5,448,513	9/1995	Hu et al.			
	4,298,962	11/1981	Hamano et al.			
	3,439,214	4/1969	Kabell			
	6,081,443	6/2000	Morishita			
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WSL	FR 2 197 494	3/1974	French			
	EP 1 180 799	2/2002	European			
	EP 0 030 856	6/1981	European			
	GB 1 414 228	11/1975	Great Britain			
	EP 0 694 977	1/1996	European			
	JP 02 294076	2/1991	Japanese			
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WSL	"The Multistable Charge-Controlled Memory Effect in SOI MOS Transistors at Low Temperatures", Tack et al., IEEE Transactions on Electron Devices, Vol. 37, No. 5, May 1990, pp.1373-1382

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WBL	5,936,265	8/1999	Koga			
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V	5,696,718	12/1997	Hartmann			

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WBL	EP 0 801 427	10/1997	European			
WBL	EP 0 513 923	11/1992	European			

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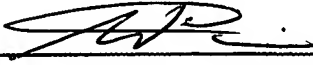
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WSL	4,298,962	11/1981	Hamano et al.			
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WSL	EP 0 731 972	11/2001	European			
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WSL	2001/0055859	12/2001	Yamada et al.			
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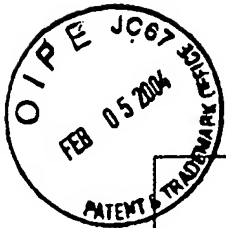
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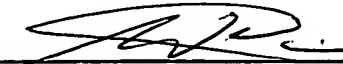
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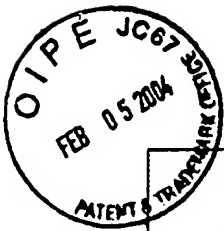
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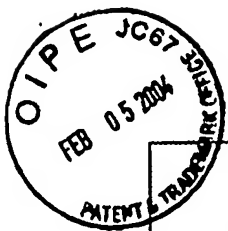
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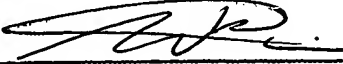
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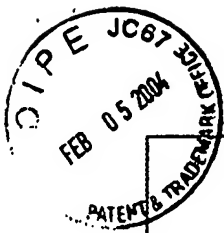
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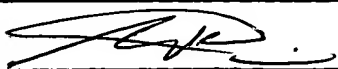
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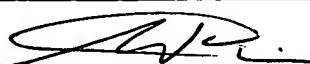
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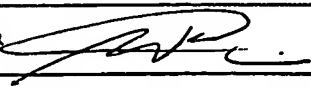
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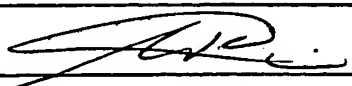
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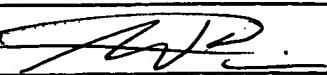
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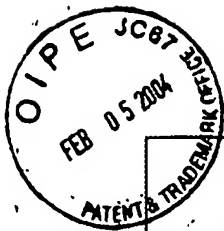
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	EP 0 465 961 B1	8/1995	European			
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	EP 0 245 515 B1	4/1997	European			
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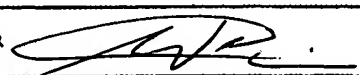
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WSL	2002/0036322	3/2002	Divakauni et al.			
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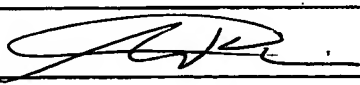
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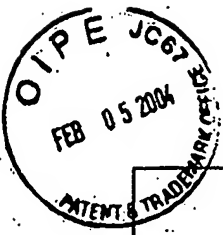
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WSL	6,297,090	10/2001	Kim			
↓	6,384,445	5/2002	Hidaka et al.			
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EXAMINER INITIALS	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES/NO
WSL	JP 62 272561	11/1987	Japanese			
↓	JP 8 274277	10/1996	Japanese			
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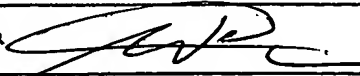
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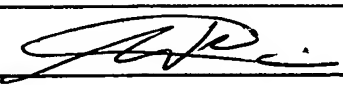
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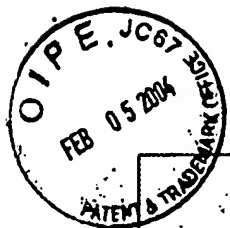
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